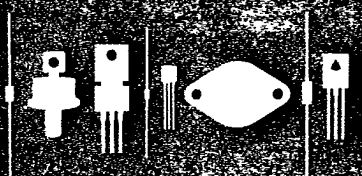


Central
Semiconductor Corp.
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145 Adams Avenue
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92 DE 1989963 0000323 2



BYX10

SILICON HIGH VOLTAGE RECTIFIER
0.5 AMP, 1600 VOLTS

CASE 101

DESCRIPTION

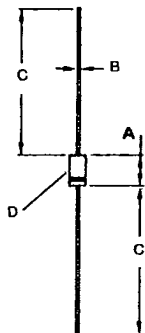
The CENTRAL SEMICONDUCTOR BYX10 type is an axial lead epoxy molded silicon rectifier designed for general purpose, very high voltage applications. For higher current applications, (up to 2.0 Amps) contact the factory for information on CR2-160 rectifier (2.0 Amps, 1600 Volts).

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>		<u>UNIT</u>
Non-Repetitive Peak Reverse Voltage ($t=10\text{ms}$)	V_{RSM}	1600	V
Peak Repetitive Reverse Voltage	V_{RRM}	1600	V
DC Blocking Voltage	V_R	1600	V
Working Reverse Voltage	V_{RWM}	800	V
Average Forward Current	$I_F(AV)$	0.5	A
Repetitive Peak Forward Current	I_{FRM}	3.0	A
Non-Repetitive Peak Forward Current ($t=10\text{ms}$, $T_A=150^\circ\text{C}$)	I_{FSM}	15	A
Peak Forward Surge Current	I_{FSM}	50	A
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +175	$^\circ\text{C}$
Typical Thermal Resistance	θ_{JA}	50	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNIT</u>
I_R	$V_R=800\text{V}$			1.0	μA
I_R	$V_R=800\text{V}$, $T_A=125^\circ\text{C}$			50	μA
I_R	$V_R=1600\text{V}$			10	μA
V_F	$I_F=1.0\text{A}$		0.9	1.1	V
V_F	$I_F=2.0\text{A}$		1.0	1.6	V



	<u>INCHES</u>		<u>mm</u>	
	<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>
A	.230	.300	5.8	7.6
B	.028	.034	0.7	0.9
C	1.0	-	25.4	-
D	.104	.140	2.6	3.6